NSN 5961-01-542-8865

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-542-8865 **Inclosure Material:** Plastic **Overall Length:** Between 0.305 inches and 0.320 inches **Terminal Length:** Between 0.030 inches and 0.050 inches **Overall Height:** Between 0.075 inches and 0.095 inches **Overall Width:** Between 0.220 inches and 0.240 inches **End Application:** Nsn 1430-01-087-6337; information and coordination central, guided missile system; w/s: missile, patriot **Mounting Method: Terminal Features Provided:** Electrostatic sensitive **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 20.0 repetitive peak reverse voltage and 20.0 working peak reverse voltage **Current Rating Per Characteristic:** 3.00 amperes collector current, dc **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Product Name:** Semiconductor device, diode - schottky power rectifier **Special Features:** Surface mount plastic smc package with j-bend leads; operating junction temperature range -65.0 to 125.0 celsius **Terminal Type And Quantity:** 2 flange Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: